

**ISOTOP<sup>®</sup> Boost chopper  
MOSFET Power Module**
 $V_{DSS} = 200V$   
 $R_{DSon} = 22m\Omega \text{ max @ } T_j = 25^\circ C$   
 $I_D = 97A \text{ @ } T_c = 25^\circ C$ 

**Application**

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

**Features**

- Power MOS V<sup>®</sup> MOSFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic diode
  - Avalanche energy rated
  - Very rugged
- ISOTOP<sup>®</sup> Package (SOT-227)
- Very low stray inductance
- High level of integration

**Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Very rugged
- Low profile
- RoHS Compliant

**Absolute maximum ratings**

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	200	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	97
		$T_c = 80^\circ C$	72
$I_{DM}$	Pulsed Drain current	388	A
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	22	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	450
$I_{AR}$	Avalanche current (repetitive and non repetitive)	97	A
$E_{AR}$	Repetitive Avalanche Energy	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy	2500	
$I_{FAV}$	Maximum Average Forward Current	Duty cycle=0.5	A
$I_{FRMS}$	RMS Forward Current (Square wave, 50% duty)	$T_c = 90^\circ C$	
			47

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 200\text{V}$	$T_j = 25^\circ\text{C}$			25	$\mu\text{A}$
		$V_{GS} = 0\text{V}, V_{DS} = 160\text{V}$	$T_j = 125^\circ\text{C}$			250	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 48.5\text{A}$				22	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$		2		4	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$				$\pm 100$	nA

**Dynamic Characteristics**

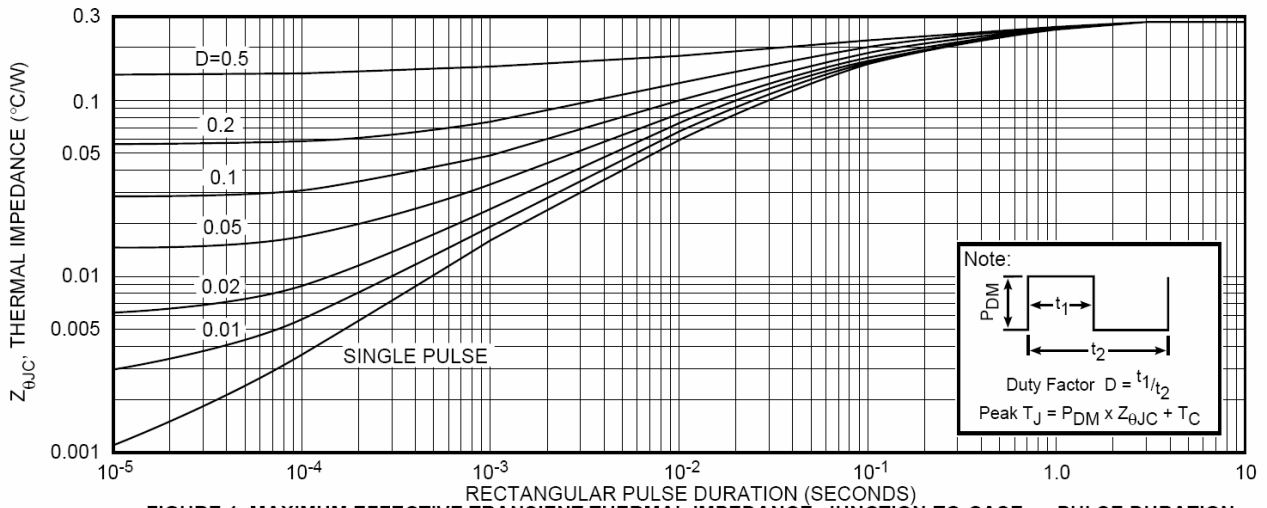
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}$			8500		pF
$C_{oss}$	Output Capacitance	$V_{DS} = 25\text{V}$			1950		
$C_{rss}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$			560		
$Q_g$	Total gate Charge	$V_{GS} = 10\text{V}$			290		nC
$Q_{gs}$	Gate – Source Charge	$V_{Bus} = 100\text{V}$			66		
$Q_{gd}$	Gate – Drain Charge	$I_D = 97\text{A} @ T_j = 25^\circ\text{C}$			120		
$T_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15\text{V}$			16		ns
$T_r$	Rise Time	$V_{Bus} = 100\text{V}$			25		
$T_{d(off)}$	Turn-off Delay Time	$I_D = 97\text{A} @ T_j = 25^\circ\text{C}$			48		
$T_f$	Fall Time	$R_G = 0.6\Omega$			8		

**Chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit	
$V_F$	Diode Forward Voltage	$I_F = 30\text{A}$			1.1	1.15	V	
		$I_F = 60\text{A}$			1.4			
		$I_F = 30\text{A}$	$T_j = 125^\circ\text{C}$		0.9			
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 200\text{V}, T_j = 25^\circ\text{C}$				250	$\mu\text{A}$	
		$V_R = 200\text{V}, T_j = 125^\circ\text{C}$				500		
$C_T$	Junction Capacitance	$V_R = 200\text{V}$			94		pF	
$t_{rr}$	Reverse Recovery Time	$I_F = 1\text{A}, V_R = 30\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		21		ns	
				$T_j = 25^\circ\text{C}$		24		
				$T_j = 125^\circ\text{C}$		48		
$I_{RRM}$	Maximum Reverse Recovery Current	$I_F = 30\text{A}$ $V_R = 133\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		3		A	
				$T_j = 125^\circ\text{C}$		6		
				$T_j = 25^\circ\text{C}$		33		
$Q_{rr}$	Reverse Recovery Charge	$I_F = 30\text{A}$ $V_R = 133\text{V}$ $di/dt = 1000\text{A}/\mu\text{s}$	$T_j = 125^\circ\text{C}$		150		nC	
				$T_j = 25^\circ\text{C}$		31		
$t_{rr}$	Reverse Recovery Time	$I_F = 30\text{A}$			31		ns	
$Q_{rr}$	Reverse Recovery Charge	$V_R = 133\text{V}$			335		nC	
$I_{RRM}$	Maximum Reverse Recovery Current	$di/dt = 1000\text{A}/\mu\text{s}$			19		A	

**Thermal and package characteristics**

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance	MOSFET		0.28	°C/W
		Diode		1.21	
$R_{thJA}$	Junction to Ambient (IGBT & Diode)			20	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case $t=1$ min, $I_{iso}<1$ mA, 50/60Hz	2500			V
$T_J, T_{STG}$	Storage Temperature Range	-55		150	°C
$T_L$	Max Lead Temp for Soldering: 0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

**Typical MOSFET Performance Curve**


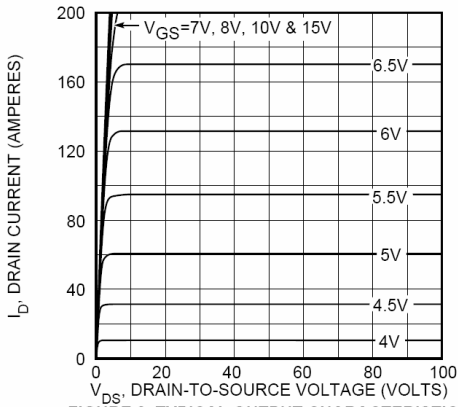


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

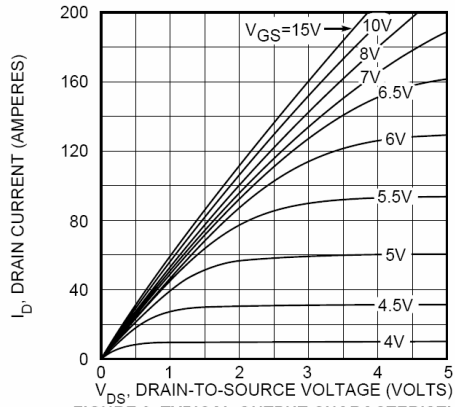


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

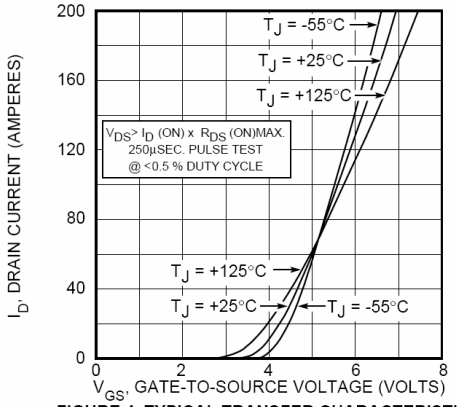


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

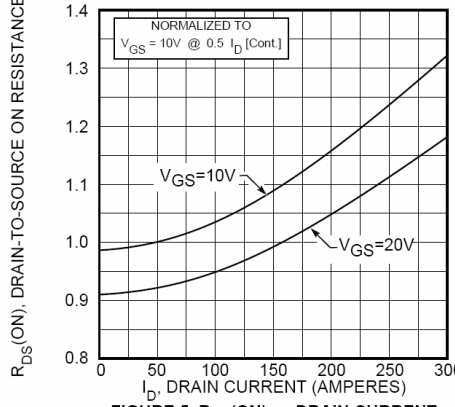


FIGURE 5,  $R_{DS(ON)}$  vs DRAIN CURRENT

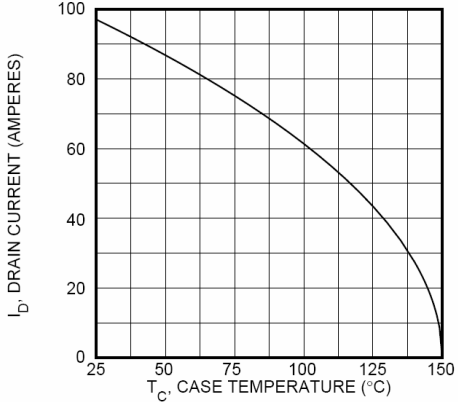


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

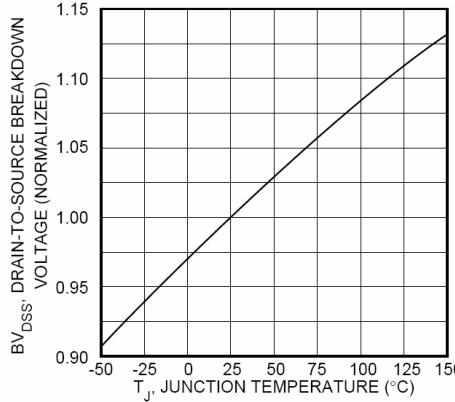


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

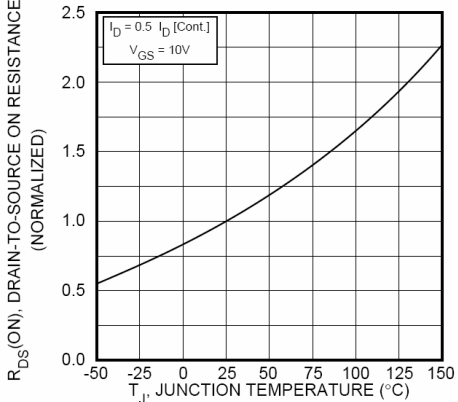


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

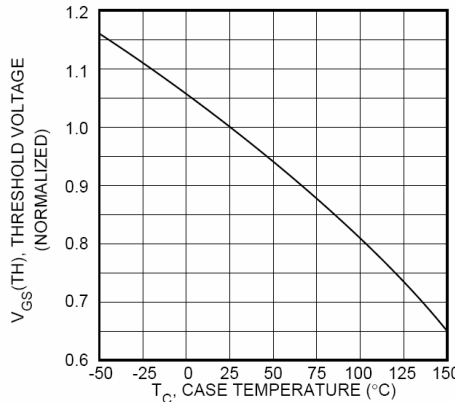


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

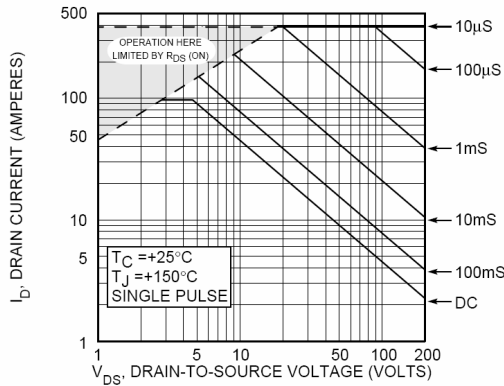


FIGURE 10, MAXIMUM SAFE OPERATING AREA

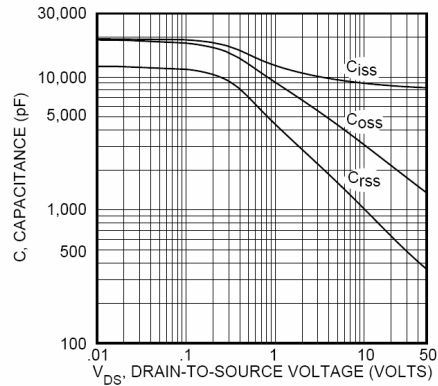


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

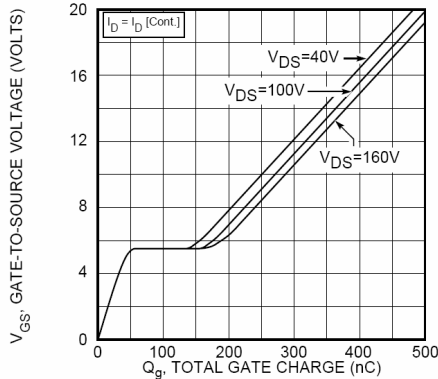


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

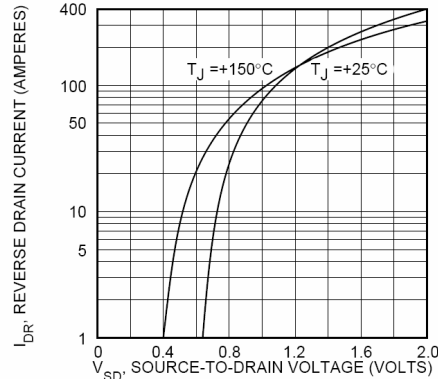


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

## Typical Diode Performance Curve

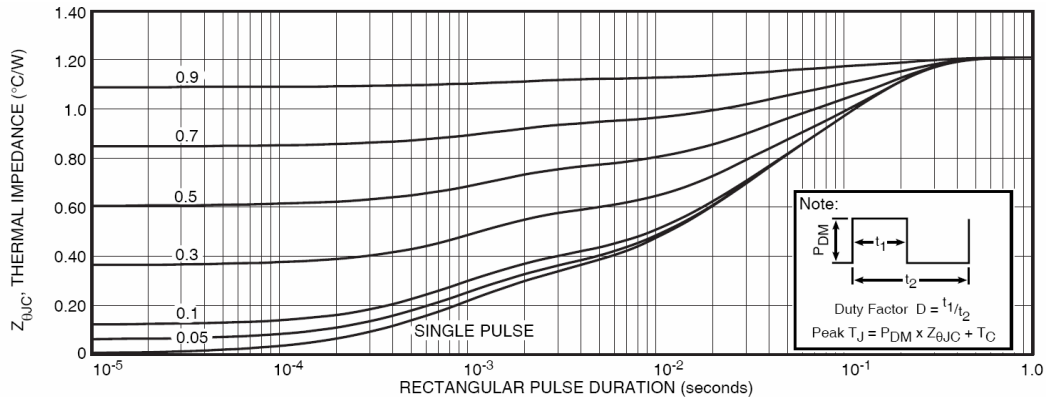


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

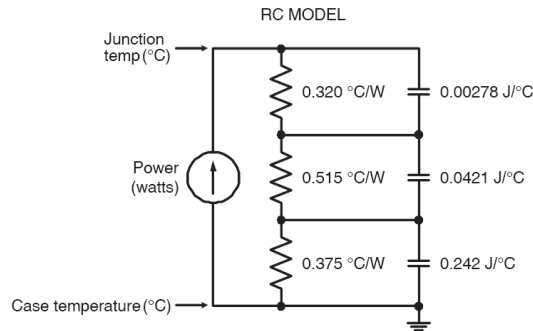


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

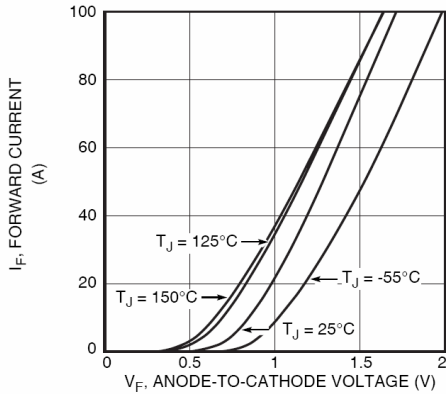


Figure 2. Forward Current vs. Forward Voltage

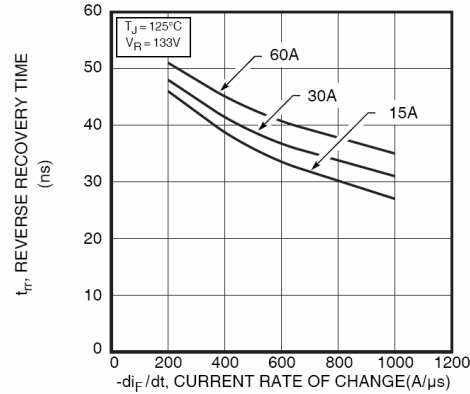


Figure 3. Reverse Recovery Time vs. Current Rate of Change

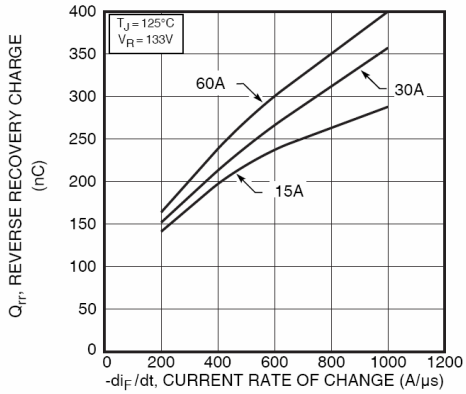


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

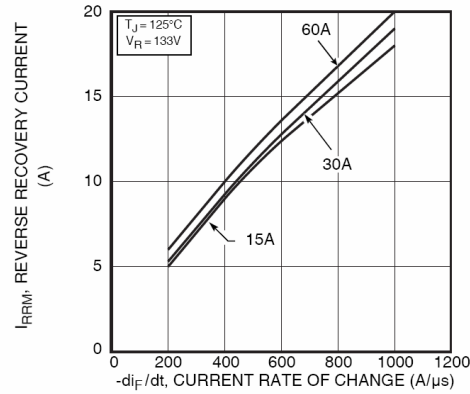


Figure 5. Reverse Recovery Current vs. Current Rate of Change

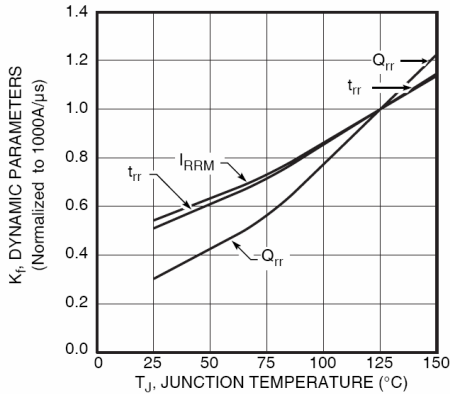


Figure 6. Dynamic Parameters vs. Junction Temperature

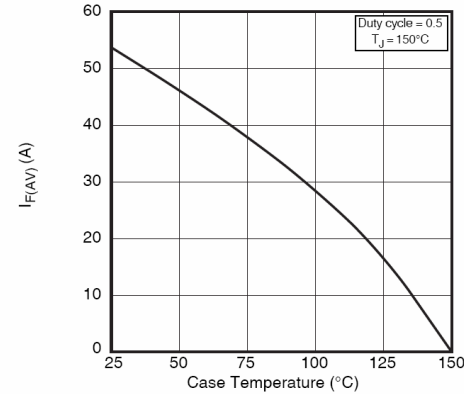


Figure 7. Maximum Average Forward Current vs. Case Temperature

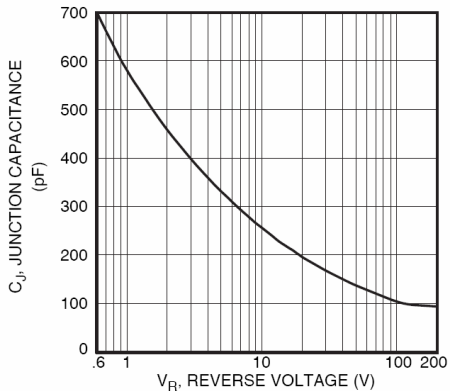


Figure 8. Junction Capacitance vs. Reverse Voltage

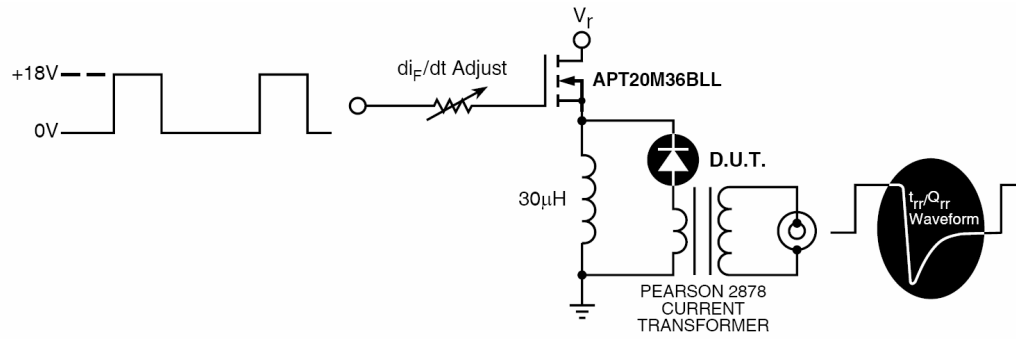


Figure 9. Diode Test Circuit

- 1  $I_F$  - Forward Conduction Current
- 2  $di_F/dt$  - Rate of Diode Current Change Through Zero Crossing.
- 3  $I_{RRM}$  - Maximum Reverse Recovery Current.
- 4  $t_{rr}$  - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through  $I_{RRM}$  and  $0.25 \cdot I_{RRM}$  passes through zero.
- 5  $Q_{rr}$  - Area Under the Curve Defined by  $I_{RRM}$  and  $t_{rr}$ .

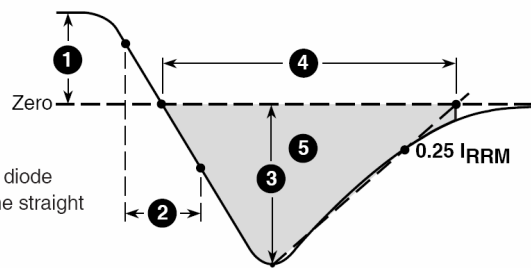
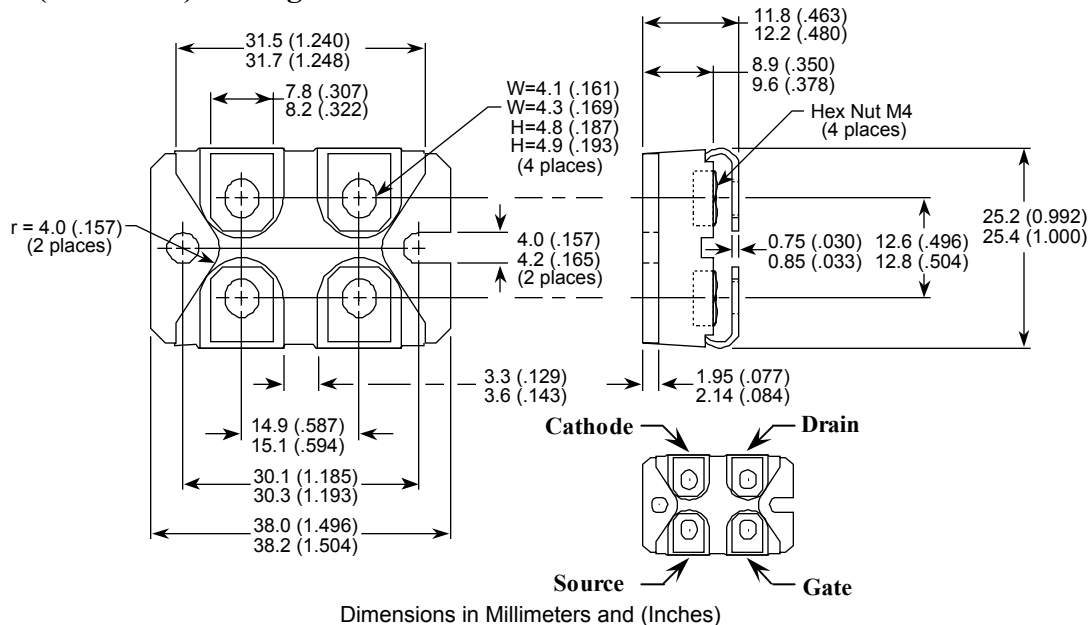


Figure 10, Diode Reverse Recovery Waveform and Definitions

## SOT-227 (ISOTOP<sup>®</sup>) Package Outline



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Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.